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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Binghua Hu, et al.

Docket No: TI-35362

Serial No: 10/712,455

Conf. No: 9290

Examiner: Laura M. Schillinger

Art Unit: 2813

Filed: 11/12/2003

For: METHOD TO MANUFACTURE LDMOS TRANSISTORS WITH IMPROVED
THRESHOLD VOLTAGE CONTROL

ELECTION

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(a)
I hereby certify that the above correspondence is being
deposited with the U.S. Postal Service with sufficient
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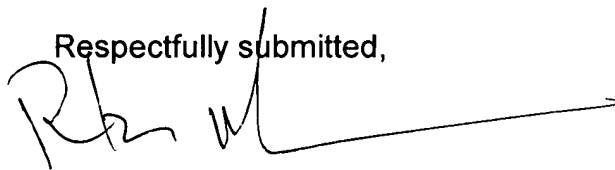

Ann Trent

Dear Sir:

This election is offered in response to the Examiner's restriction requirement
mailed June 21, 2005.

Applicants hereby elect to pursue Species 3 of Claims 8-10, pertaining to a
method for forming LDMOS transistors including forming a deep n-well region and
forming LOCOS isolation structures, without traversing the Examiner's restriction
requirement.

Respectfully submitted,



Peter K. McLarty
Attorney for Applicants
Reg. No. 44,923

Texas Instruments Incorporated
P.O. Box 655474, MS 3999
Dallas, TX 75265
(972) 917-4258